

## Six-Pack XPT IGBT

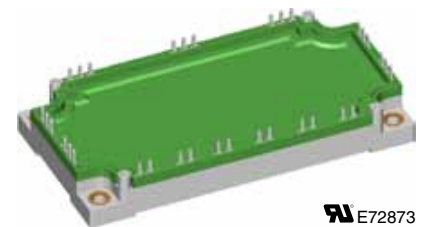
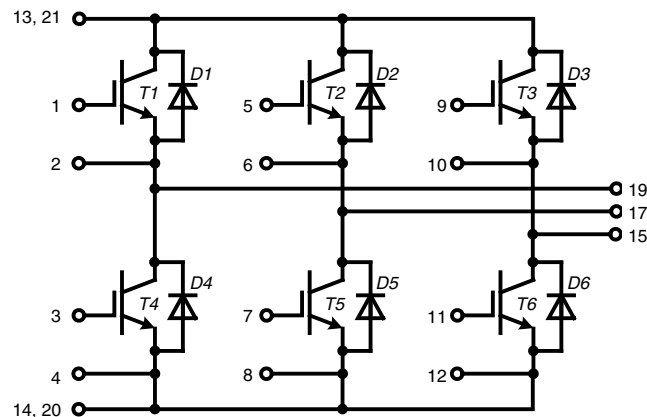
$$V_{CES} = 1200 \text{ V}$$

$$I_{C25} = 155 \text{ A}$$

$$V_{CE(sat)} = 1.8 \text{ V}$$

**Part name** (Marking on product)

MIXA101W1200EH



### Features:

- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
  - short circuit rated for 10  $\mu$ sec.
  - very low gate charge
  - square RBSOA @ 3x  $I_C$
  - low EMI
- Thin wafer technology combined with the XPT design results in a competitive low  $V_{CE(sat)}$
- SONIC™ diode
  - fast and soft reverse recovery
  - low operating forward voltage

### Application:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies

### Package:

- "E3-Pack" standard outline
- Insulated copper base plate
- Soldering pins for PCB mounting
- Optimizes pin layout

## Output Inverter T1 - T6

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
$V_{CES}$	collector emitter voltage				1200	V
$V_{GES}$	max. DC gate voltage	continuous			±20	V
$V_{GEM}$	max. transient collector gate voltage	transient			±30	V
$I_{C25}$	collector current				155	A
$I_{C80}$					108	A
$P_{tot}$	total power dissipation				500	W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 100\text{ A}; V_{GE} = 15\text{ V}$		1.8	2.1	V
				2.1		V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 4\text{ mA}; V_{GE} = V_{CE}$		5.4	6.0	V
$I_{CES}$	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$		0.03	0.3	mA
				0.6		mA
$I_{GES}$	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$			500	nA
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 100\text{ A}$		295		nC
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{ V}; I_C = 100\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 7\ \Omega$	$T_{VJ} = 125^\circ\text{C}$		70	ns
$t_r$	current rise time				40	ns
$t_{d(off)}$	turn-off delay time				250	ns
$t_f$	current fall time				100	ns
$E_{on}$	turn-on energy per pulse				8.5	mJ
$E_{off}$	turn-off energy per pulse				11	mJ
<b>RBSOA</b>	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 7\ \Omega;$			300	A
<b>SCSOA</b>	short circuit safe operating area					
$t_{SC}$	short circuit duration	$V_{CE} = 900\text{ V}; V_{GE} = \pm 15\text{ V};$			10	$\mu\text{s}$
$I_{SC}$	short circuit current	$R_G = 7\ \Omega;$ non-repetitive		400		A
$R_{thJC}$	thermal resistance junction to case	(per IGBT)			0.25	K/W

## Output Inverter D1 - D6

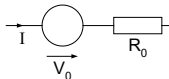
Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
$V_{RRM}$	max. repetitive reverse voltage				1200	V
$I_{F25}$	forward current				135	A
$I_{F80}$					90	A
$V_F$	forward voltage	$I_F = 100\text{ A}; V_{GE} = 0\text{ V}$		1.95	2.2	V
				1.95		V
$Q_{rr}$	reverse recovery charge	$V_R = 600\text{ V}$ $di_F/dt = -1600\text{ A}/\mu\text{s}$ $I_F = 100\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 125^\circ\text{C}$		12.5	$\mu\text{C}$
$I_{RM}$	max. reverse recovery current				100	A
$t_{rr}$	reverse recovery time				350	ns
$E_{rec}$	reverse recovery energy				4	mJ
$R_{thJC}$	thermal resistance junction to case	(per diode)			0.4	K/W

 $T_C = 25^\circ\text{C}$  unless otherwise stated

## Module

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
$T_{VJ}$	operating temperature		-40		125	°C
$T_{VJM}$	max. virtual junction temperature				150	°C
$T_{stg}$	storage temperature		-40		125	°C
$V_{ISOL}$	isolation voltage	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}$			3000	V~
CTI	comparative tracking index				200	
$M_d$	mounting torque (M5)		3		6	Nm
$d_s$	creep distance on surface		10			mm
$d_A$	strike distance through air		7.5			mm
$R_{pin-chip}$	resistance pin to chip			2.5		mΩ
$R_{thCH}$	thermal resistance case to heatsink	with heatsink compound		0.02		K/W
Weight				300		g

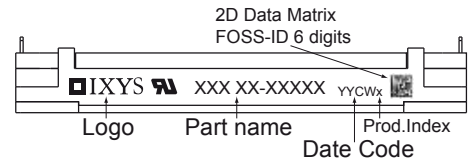
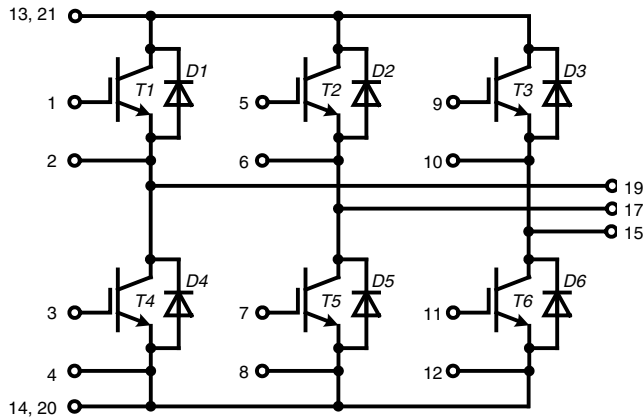
## Equivalent Circuits for Simulation



Symbol	Definitions	Conditions		Ratings			Unit
				min.	typ.	max.	
$V_0$	IGBT	T1 - T6	$T_{VJ} = 150^\circ\text{C}$			1.1	V
$R_0$						13.8	mΩ
$V_0$	free wheeling diode	D1 - D6	$T_{VJ} = 150^\circ\text{C}$			1.25	V
$R_0$						8.5	mΩ

$T_C = 25^\circ\text{C}$  unless otherwise stated

## Circuit Diagram

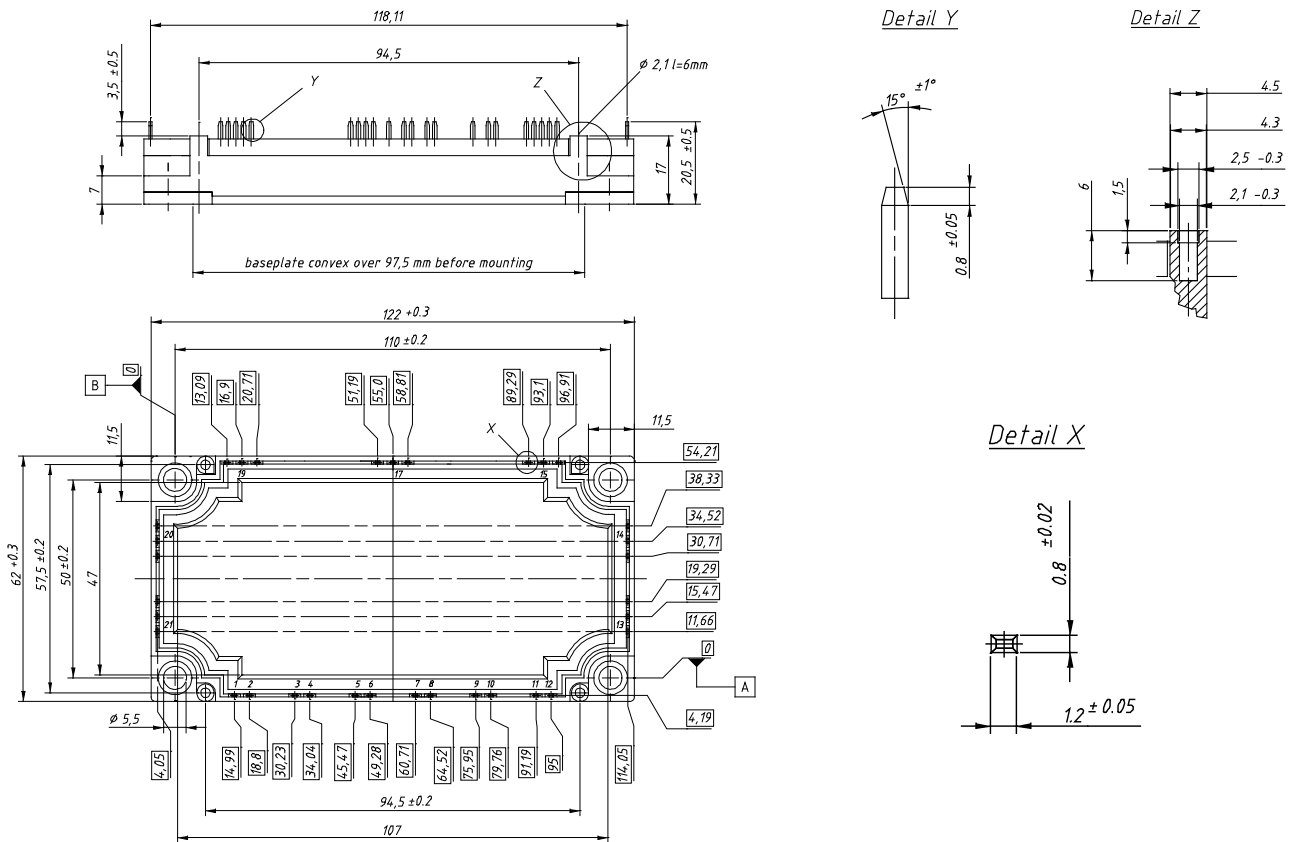


### Part number

- M = Module
- I = IGBT
- X = XPT
- A = standard
- 101 = Current Rating [A]
- W = Six-Pack
- 1200 = Reverse Voltage [V]
- EH = E3-Pack

## Outline Drawing

Dimensions in mm (1 mm = 0.0394")



## Product Marking

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MIXA101W1200EH	MIXA101W1200EH	Box	5	511591

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## Transistor T1 - T6

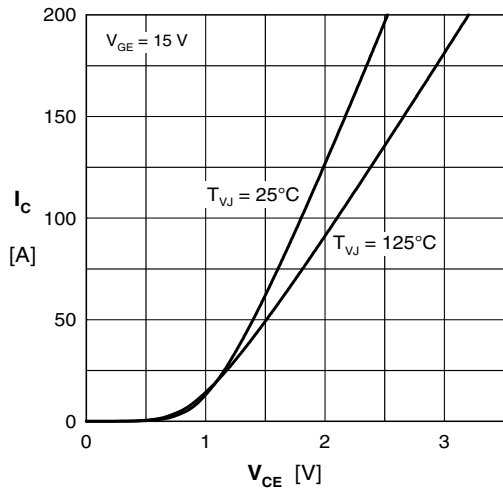


Fig. 1 Typ. output characteristics

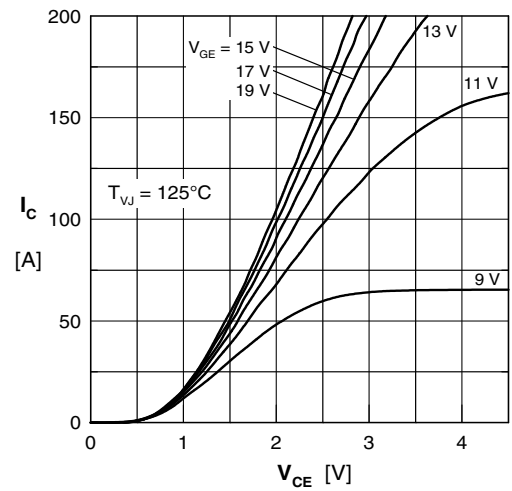


Fig. 2 Typ. output characteristics

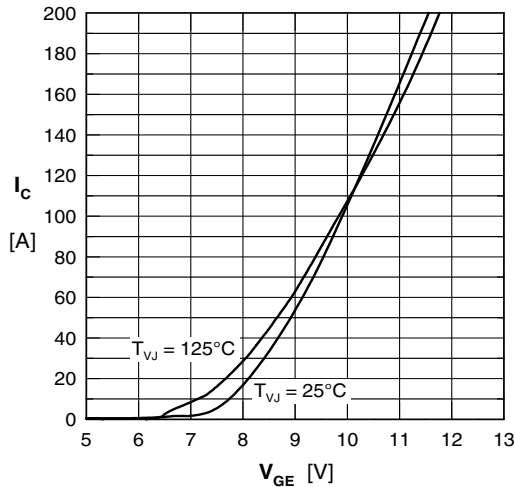


Fig. 3 Typ. transfer characteristics

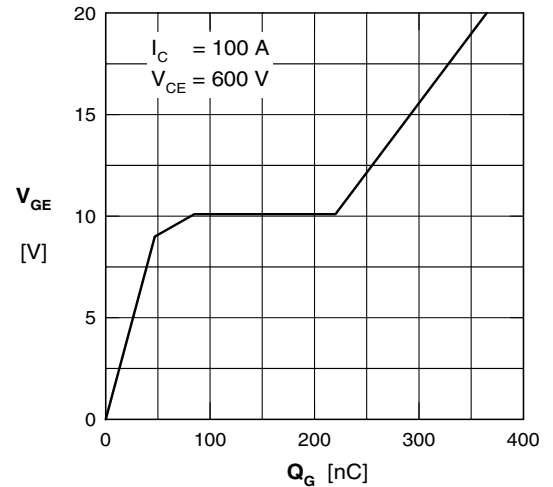


Fig. 4 Typ. turn-on gate charge

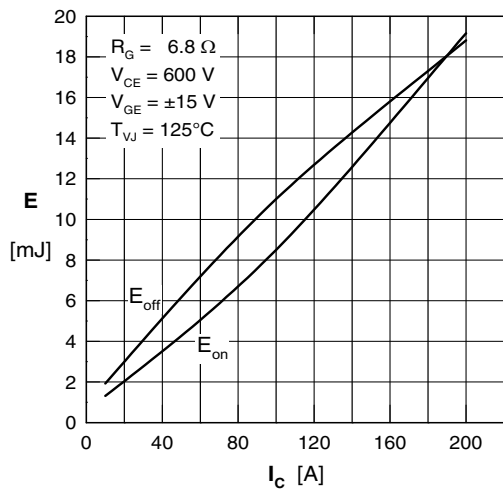


Fig. 5 Typ. switching energy vs. collector current

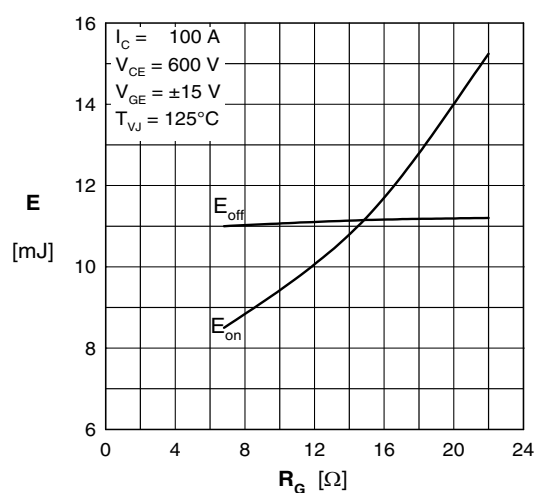


Fig. 6 Typ. switching energy vs. gate resistance

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## Inverter D1 - D6

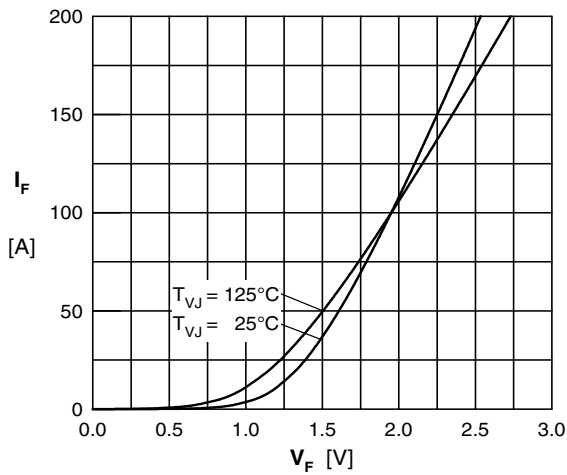


Fig. 7 Typ. Forward current versus  $V_F$

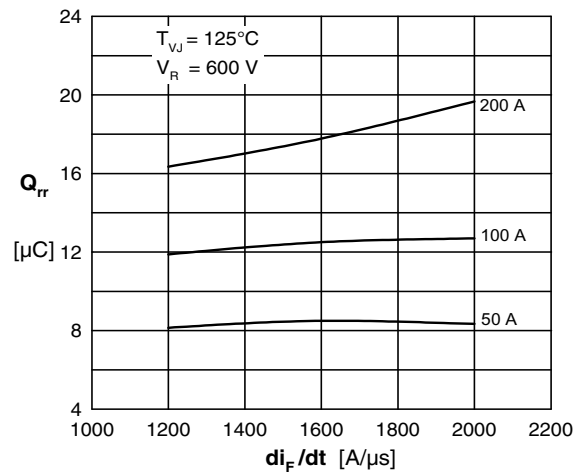


Fig. 8 Typ. reverse recov.charge  $Q_{rr}$  vs.  $di/dt$

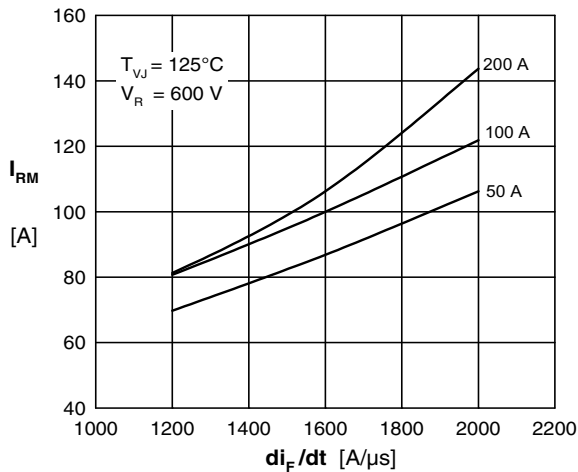


Fig. 9 Typ. peak reverse current  $I_{RM}$  vs.  $di/dt$

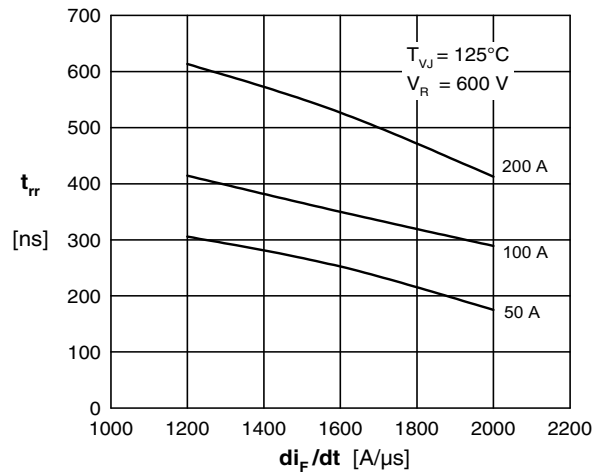


Fig. 10 Typ. recovery time  $t_{rr}$  versus  $di/dt$

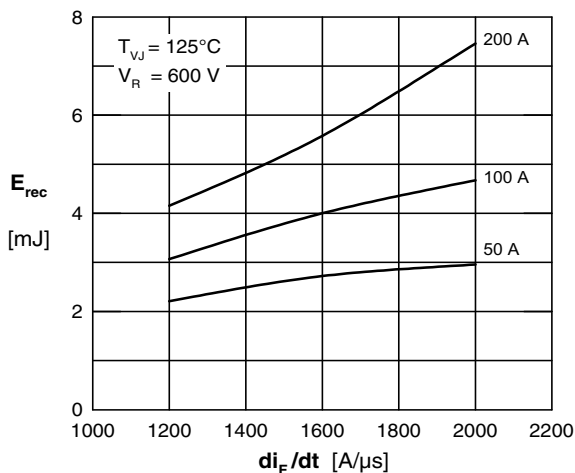


Fig. 11 Typ. recovery energy  $E_{rec}$  versus  $di/dt$

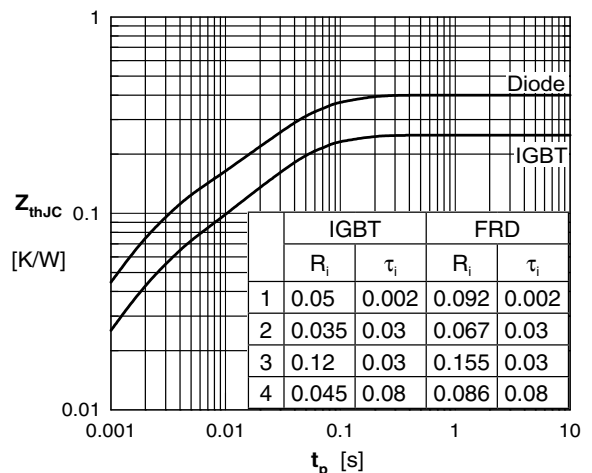


Fig. 12 Typ. transient thermal impedance